# INTEGRATED CIRCUITS



Product specification Supersedes data of 1995 Aug 17 IC23 Data Handbook 1998 Feb 27





## 74ABT16543 74ABTH16543

#### FEATURES

- Two 8-bit octal transceivers with D-type latch
- Live insertion/extraction permitted
- Power-up 3-State
- Power-up reset
- Multiple V<sub>CC</sub> and GND pins minimize switching noise
- Back-to-back registers for storage
- Separate controls for data flow in each direction
- 74ABTH16543 incorporates bus-hold data inputs which eliminate the need for external pull-up resistors to hold unused inputs
- Output capability: +64mA/-32mA
- Latch-up protection exceeds 500mA per JEDEC Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model
- See 74ABT161543 for same function with Master Reset control pins

### QUICK REFERENCE DATA

#### DESCRIPTION

The 74ABT16543 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT16543 16-bit registered transceiver contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate Latch Enable (nLEAB, nLEBA) and Output Enable (nDEAB, nDEBA) inputs are provided for each register to permit independent control of data transfer in either direction. The outputs are guaranteed to sink 64mA.

Two options are available, 74ABT16543 which does not have the bus-hold feature and 74ABTH16543 which incorporates the bus-hold feature.

SYMBOL	PARAMETER	CONDITIONS T <sub>amb</sub> = 25°C; GND = 0V	TYPICAL	UNIT
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay nAx to nBx	$C_L = 50 pF; V_{CC} = 5V$	2.5 2.2	ns
C <sub>IN</sub>	Input capacitance	$V_I = 0V \text{ or } V_{CC}$	3	pF
C <sub>I/O</sub>	I/O capacitance	V <sub>O</sub> = 0V or V <sub>CC</sub> ; 3-State	7	pF
I <sub>CCZ</sub>	Quiescent supply current	Outputs disabled; V <sub>CC</sub> = 5.5V	550	μΑ
I <sub>CCL</sub>	Quescent supply current	Outputs low; $V_{CC} = 5.5V$	9	mA

#### ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
56-Pin Plastic SSOP Type III	–40°C to +85°C	74ABT16543 DL	BT16543 DL	SOT371-1
56-Pin Plastic TSSOP Type II	–40°C to +85°C	74ABT16543 DGG	BT16543 DGG	SOT364-1
56-Pin Plastic SSOP Type III	–40°C to +85°C	74ABTH16543 DL	BH16543 DL	SOT371-1
56-Pin Plastic TSSOP Type II	–40°C to +85°C	74ABTH16543 DGG	BH16543 DGG	SOT364-1

#### **PIN DESCRIPTION**

PIN NUMBER	SYMBOL	NAME AND FUNCTION
5, 6, 8, 9, 10, 12, 13, 14 15, 16, 17, 19, 20, 21, 23, 24	1A0 – 1A7, 2A0 – 2A7	Data inputs/outputs
52, 51, 49, 48, 47, 45, 44, 43 42, 41, 40,38, 37, 36, 34, 33	1B0 – 1B7, 2B0 – 2B7	Data inputs/outputs
1, 56 28, 29	1 <u>OEAB</u> , 1 <u>OEBA,</u> 2 <u>OEAB</u> , 2 <u>OEBA</u>	A to B / B to A Output Enable inputs (active-Low)
3, 54 26, 31	1EAB, 1EBA, 2EAB, 2EBA	A to B / B to A Enable inputs (active-Low)
2, 55 27, 30	1LEAB, 1LEBA, 2LEAB, 2LEBA	A to B / B to A Latch Enable inputs (active-Low)
4, 11, 18, 25, 32, 39, 46, 53	GND	Ground (0V)
7, 22, 35, 50	V <sub>CC</sub>	Positive supply voltage

### LOGIC SYMBOL (IEEE/IEC)



PIN CONFIGURAT	ION		
1 OEAB	1	56	10EBA
1LEAB	2	55	1LEBA
1EAB	3	54	1EBA
GND	4	53	GND
1A0	5	52	1B0
1A1	6	51	1B1
VCC	7	50	VCC
1A2	8	49	1B2
1A3	9	48	1B3
1A4	10	47	1B4
GND	11	46	GND
1A5	12	45	1B5
1A6	13	44	1B6
1A7	14	43	1B7
2A0	15	42	2B0
2A1	16	41	2B1
2A2	17	40	2B2
GND	18	39	GND
2A3	19	38	2B3
2A4	20	37	2B4
2A5	21	36	2B5
VCC	22	35	VCC
2A6	23	34	2B6
2A7	24	33	2B7
GND	25	32	GND
2EAB	26	31	2EBA
2LEAB	27	30	2LEBA
20EAB	28	29	20EBA
	SH00	037	
	3/100		

## **PIN CONFIGURATION**

### LOGIC SYMBOL



### **FUNCTIONAL DESCRIPTION**

The 74ABT16543 contains two sets of eight D-type latches, with separate control pins for each set. Using data flow from A to B as an example, when the A-to-B Enable (nEAB) input and the A-to-B Latch Enable (nEAB) input are Low the A-to-B path is transparent.

A subsequent Low-to-High transition of the nLEAB signal puts the A data into the latches where it is stored and the B outputs no longer change with the A inputs. With EAB and nOEAB both Low, the 3-State B output buffers are active and display the data present at the outputs of the A latches.

Control of data flow from B to A is similar, but using the nEBA, nLEBA, and nOEBA inputs.

#### FUNCTION TABLE

	INF	PUTS		OUTPUTS	STATUS
nOEXX	nEXX	nLEXX	nAx or nBx	nBx or nAx	STATUS
Н	Х	Х	Х	Z	Disabled
Х	Н	Х	Х	Z	Disabled
L	$\stackrel{}{\leftarrow}$		h I	Z Z	Disabled + Latch
L	L	$\stackrel{}{\leftarrow}$	h I	H L	Latch + Display
L	L	L	H L	H L	Transparent
L	L	Н	Х	NC	Hold

H = High voltage level

h = High voltage level one set-up time prior to the Low-to-High transition of nLEXX or nEXX (XX = AB or BA)

L = Low voltage level

I = Low voltage level one set-up time prior to the Low-to-High transition of nLEXX or nEXX (XX = AB or BA)

X = Don't care

 $\uparrow = Low-to-High transition of n \overline{LEXX} or n \overline{EXX} (XX = AB or BA)$ 

NC= No change

Z = High impedance or "off" state

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### LOGIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS<sup>1, 2</sup>

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V <sub>CC</sub>	DC supply voltage		-0.5 to +7.0	V
I <sub>IK</sub>	DC input diode current	V <sub>I</sub> < 0	-18	mA
VI	DC input voltage <sup>3</sup>		-1.2 to +7.0	V
I <sub>ОК</sub>	DC output diode current	V <sub>O</sub> < 0	-50	mA
V <sub>OUT</sub>	DC output voltage <sup>3</sup>	output in Off or High state	–0.5 to +5.5	V
		output in Low state	128	mA
IOUT	DC output current	output in High state	-64	mA
T <sub>stg</sub>	Storage temperature range		-65 to 150	°C

NOTES:

 Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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### **RECOMMENDED OPERATING CONDITIONS**

SYMBOL	PARAMETER	LIM	UNIT	
STMBOL	TANAMETER	Min	Max	UNIT
V <sub>CC</sub>	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V <sub>CC</sub>	V
V <sub>IH</sub>	High-level input voltage	2.0		V
VIL	Low-level Input voltage		0.8	V
I <sub>OH</sub>	High-level output current		-32	mA
I <sub>OL</sub>	Low-level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T <sub>amb</sub>	Operating free-air temperature range	-40	+85	°C

## **DC ELECTRICAL CHARACTERISTICS**

		ER TEST CONDITIONS							
SYMBOL	PARAMETER			Ta	amb = +25	°C	T <sub>amb</sub> = -40°C to +85°C		UNIT
				MIN	TYP	MAX	MIN	MAX	1
V <sub>IK</sub>	Input clamp voltage	V <sub>CC</sub> = 4.5V; I <sub>IK</sub> = -18mA				-1.2		-1.2	V
		$V_{CC}$ = 4.5V; $I_{OH}$ = -3mA; $V_I$ = $V_{IL}$ c	or V <sub>IH</sub>	2.5	2.9		2.5		V
V <sub>OH</sub>	High-level output voltage	$V_{CC}$ = 5.0V; $I_{OH}$ = -3mA; $V_{I}$ = $V_{IL}$ c	or V <sub>IH</sub>	3.0	3.4		3.0		V
		$V_{CC}$ = 4.5V; $I_{OH}$ = -32mA; $V_I$ = $V_{IL}$	or V <sub>IH</sub>	2.0	2.4		2.0		V
V <sub>OL</sub>	Low-level output voltage	$V_{CC}$ = 4.5V; $I_{OL}$ = 64mA; $V_{I}$ = $V_{IL}$ o	r V <sub>IH</sub>		0.36	0.55		0.55	V
V <sub>RST</sub>	Power-up output voltage <sup>3</sup>	$V_{CC} = 5.5V; I_{O} = 1mA; V_{I} = GND$ of	r V <sub>CC</sub>		0.13	0.55		0.55	V
łı	Input leakage current	$V_{CC}$ = 5.5V; $V_{I}$ = GND or 5.5V	Control pins		±0.01	±1.0		±1.0	μΑ
		$V_{CC} = 4.5V; V_{I} = 0.8V$	•	35			35		
I <sub>HOLD</sub>	Bus Hold current A or B Ports <sup>5</sup> 74ABTH16543	$V_{CC} = 4.5V; V_{I} = 2.0V$		-75			-75		μA
		$V_{CC} = 5.5V; V_I = 0 \text{ to } 5.5V$		±800					
I <sub>OFF</sub>	Power-off leakage current	$V_{CC}$ = 0.0V; $V_O$ or $V_I \leq 4.5V$			±2.0	±100		±100	μΑ
I <sub>PU/PD</sub>	Power-up/down 3-State output current <sup>4</sup>	$V_{CC}$ = 2.1V; $V_{O}$ = 0.0V or $V_{CC}$ ; $V_{I}$ = GND or $V_{CC}$ ; $V_{OE}$ = Don't care	)		±1.0	±50		±50	μΑ
I <sub>IH</sub> + I <sub>OZH</sub>	3-State output High current	$V_{CC} = 5.5V; V_{O} = 5.5V; V_{I} = V_{IL} \text{ or}$	V <sub>IH</sub>		1.0	10		10	μΑ
I <sub>IL</sub> + I <sub>OZL</sub>	3-State output Low current	$V_{CC} = 5.5V; V_O = 0.0V; V_I = V_{IL} \text{ or}$	VIH		-1.0	-10		-10	μΑ
I <sub>CEX</sub>	Output High leakage current	$V_{CC} = 5.5V; V_{O} = 5.5V; V_{I} = GND c$	or V <sub>CC</sub>		1.0	50		50	μΑ
Ι <sub>Ο</sub>	Output current <sup>1</sup>	$V_{CC} = 5.5V; V_O = 2.5V$		-50	-100	-200	-50	-200	mA
I <sub>CCH</sub>		$V_{CC}$ = 5.5V; Outputs High, $V_I$ = GN	D or V <sub>CC</sub>		0.55	2		2	mA
I <sub>CCL</sub>	Quiescent supply current	$V_{CC}$ = 5.5V; Outputs Low, $V_{I}$ = GNI	D or V <sub>CC</sub>		9	19		19	mA
I <sub>CCZ</sub>		$V_{CC} = 5.5V$ ; Outputs 3–State; $V_I = GND \text{ or } V_{CC}$			0.55	2		2	mA
$\Delta I_{CC}$	Additional supply current per input pin <sup>2</sup> 74ABT16543	$V_{CC}$ = 5.5V; one input at 3.4V, other inputs at $V_{CC}$ or GND			5.0	50		50	μΑ
$\Delta I_{CC}$	Additional supply current per input pin <sup>2</sup> 74ABTH16543	$V_{CC}$ = 5.5V; one input at 3.4V, other inputs at $V_{CC}$ or GND			200	500		500	μΑ

#### NOTES:

1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

2. This is the increase in supply current for each input at 3.4V.

3. For valid test results, data must not be loaded into the flip-flops (or latches) after applying the power. 4. This parameter is valid for any V<sub>CC</sub> between 0V and 2.1V, with a transition time of up to 10msec. From V<sub>CC</sub> = 2.1V to V<sub>CC</sub> = 5V  $\pm$  10% a transition time of up to 100µsec is permitted.5. This is the bus hold overdrive current required to force the input to the opposite logic state.

#### **AC CHARACTERISTICS**

GND = 0V,  $t_{R}$  =  $t_{F}$  = 2.5ns,  $C_{L}$  = 50pF,  $R_{L}$  = 500 $\Omega$ 

					LIMITS			
SYMBOL	PARAMETER	WAVEFORM	۲ ۱	√ <sub>amb</sub> = +25° V <sub>CC</sub> = +5.0\	с /	T <sub>amb</sub> = -4 V <sub>CC</sub> = +5	0 to +85°C .0V ±0.5V	UNIT
			MIN	TYP	MAX	MIN	MAX	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay nAx to nBx, nBx to nAx	2	1.0 1.0	2.5 2.2	3.3 4.4	1.0 1.0	3.8 5.1	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay LEBA to nAx, LEAB to nBx	1, 2	1.0 1.2	3.1 3.0	4.3 4.8	1.0 1.2	5.2 5.6	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output enable time OEBA to nAx, OEAB to nBx	4 5	1.0 1.1	3.3 3.3	4.3 5.9	1.0 1.1	5.2 7.0	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output disable time OEBA to nAx, OEAB to nBx	4 5	1.9 1.6	3.5 2.6	5.0 4.2	1.9 1.6	5.7 4.6	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output enable time EBA to nAx, EAB to nBx	4 5	1.0 1.2	3.4 3.4	4.9 6.5	1.0 1.2	6.2 7.8	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output disable time EBA to nAx, EAB to nBx	4 5	2.0 1.7	3.4 2.6	5.6 5.1	2.0 1.7	6.6 5.4	ns

#### AC SETUP REQUIREMENTS

GND = 0V,  $t_R = t_F = 2.5ns$ ,  $C_L = 50pF$ ,  $R_L = 500\Omega$ 

				LIN	IITS	
SYMBOL	PARAMETER	WAVEFORM	T <sub>amb</sub> = V <sub>CC</sub> =	= +25°C = +5.0V	T <sub>amb</sub> = −40 to +85°C V <sub>CC</sub> = +5.0V ±0.5V	UNIT
			MIN	TYP	MIN	
t <sub>s</sub> (H) t <sub>s</sub> (L)	Setup time nAx to LEAB, nBx to LEBA	3	1.5 3.5	0.4 0.1	1.5 3.5	ns
t <sub>h</sub> (H) t <sub>h</sub> (L)	Hold time nAx to LEAB, nBx to LEBA	3	1.5 2.0	0.2 0.3	1.5 2.0	ns
t <sub>s</sub> (H) t <sub>s</sub> (L)	Setup time nAx to EAB, nBx to EBA	3	1.5 3.5	0.2 0.3	1.5 3.5	ns
t <sub>h</sub> (H) t <sub>h</sub> (L)	Hold time nAx to $\overline{EAB}$ , nBx to $\overline{EBA}$	3	1.5 2.0	0.3 0.2	1.5 2.0	ns
t <sub>w</sub> (L)	Latch enable pulse width, Low	3	4.0	3.1	4.0	ns

## AC WAVEFORMS

 $V_{M}$  = 1.5V,  $V_{IN}$  = GND to 3.0V



Waveform 1. Propagation Delay For Inverting Output





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## AC WAVEFORMS (Continued)



Waveform 3. Data Setup and Hold Times and Latch Enable Pulse Width



Waveform 4. 3-State Output Enable Time to High Level and Output Disable Time from High Level

## **TEST CIRCUIT AND WAVEFORMS**



Waveform 5. 3-State Output Enable Time to Low Level and Output Disable Time from Low Level



### DEFINITIONS

- R<sub>L</sub> = Load resistor; see AC CHARACTERISTICS for value.
- $\label{eq:CL} \begin{array}{ll} C_L = & Load \mbox{ capacitance includes jig and probe capacitance;} \\ & see \mbox{ AC CHARACTERISTICS for value.} \end{array}$
- $\label{eq:RT} \mathsf{R}_{\mathsf{T}} = \quad \text{Termination resistance should be equal to } \mathsf{Z}_{\mathsf{OUT}} \text{ of } \\ \text{pulse generators.}$

	INPUT PULSE REQUIREMENTS						
FAMILY	Amplitude	Rep. Rate	t <sub>W</sub>	t <sub>R</sub>	t <sub>F</sub>		
74ABT/H16	3.0V	1MHz	500ns	2.5ns	2.5ns		

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#### Product specification

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NOTES

#### Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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